TECH PUBLIC
台舟电子

TPBC848S

NPN+NPN Plastic-Encapsulate Transistors

www.sot23.com.tw

Features

- High current gain
- Excellent h_{FE} linearity
- Low noise

Mechanical data

- Case: SOT-363
- Molding compound: UL flammability classification rating 94V-0
- Terminals: Tin-plated; solderability per MIL-STD-202, Method 208

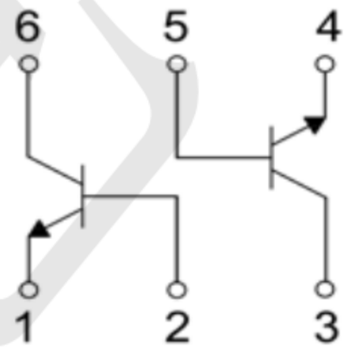
Ordering Information

- Shipping Qty:3000/7inch Tape& Reel

SOT363

Marking: 2C Or 1K

Circuit Diagram



Absolute Maximum Ratings (Tamb=25°C unless otherwise specified)

Parameter	Symbol	TPBC848S	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current (Continuous)	I_C	100	mA
Collector Current (Peak)	I_{CM}	200	mA

Thermal Characteristics

Parameter	Symbol	Value	Unit
Power Dissipation (Collector)	P_D	300	mW
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	417	°C/W
Thermal Resistance Junction-to-Case *1	$R_{\theta JC}$	260	°C/W
Thermal Resistance Junction-to-Lead *1	$R_{\theta JL}$	320	°C/W
Operating Junction Temperature	T_J	-55 ~ +150	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C

Electrical Characteristics NPN 4401(TA=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 10μA, I_E = 0	30	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 10mA, I_B = 0	30	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 10μA, I_C = 0	5	-	-	V
Collector Cut-off Current	I_{CBO}	V_{CB} = 30V, I_E = 0	-	-	15	nA
		V_{CB} = 30V, I_E = 0 T_J = 150°C	-	-	5	μA
Emitter-base Cut-off Current	I_{EBO}	V_{EB} = 5V, I_C = 0	-	-	100	nA
Collector-emitter Cut-off Current	I_{CEO}	V_{CE}= 30V, I_B = 0	-	-	1	mA
DC Current Gain	h_{FE}	V_{CE} = 5V, I_C = 10μA	-	250	-	-
DC Current Gain		V_{CE} = 5V, I_C = 2mA	200	-	450	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 10mA, I_B = 0.5mA	-	0.09	0.25	V
		I_C = 100mA, I_B = 5mA	-	0.20	0.60	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 10mA, I_B = 0.5mA	-	0.70	0.90	V
		I_C = 100mA, I_B = 5mA	-	0.90	1.10	V
Base-Emitter Voltage	$V_{BE(ON)}$	V_{CE} = 5V, I_C= 2mA	0.58	0.66	0.70	V
		V_{CE} = 5V, I_C= 10mA	-	-	0.77	V
Transition Frequency	f_T	V_{CE} = 5V, I_C= 10mA f = 100MHz	100	-	-	MHz

Typical Performance Characteristics (T_A=25°C unless otherwise Specified)

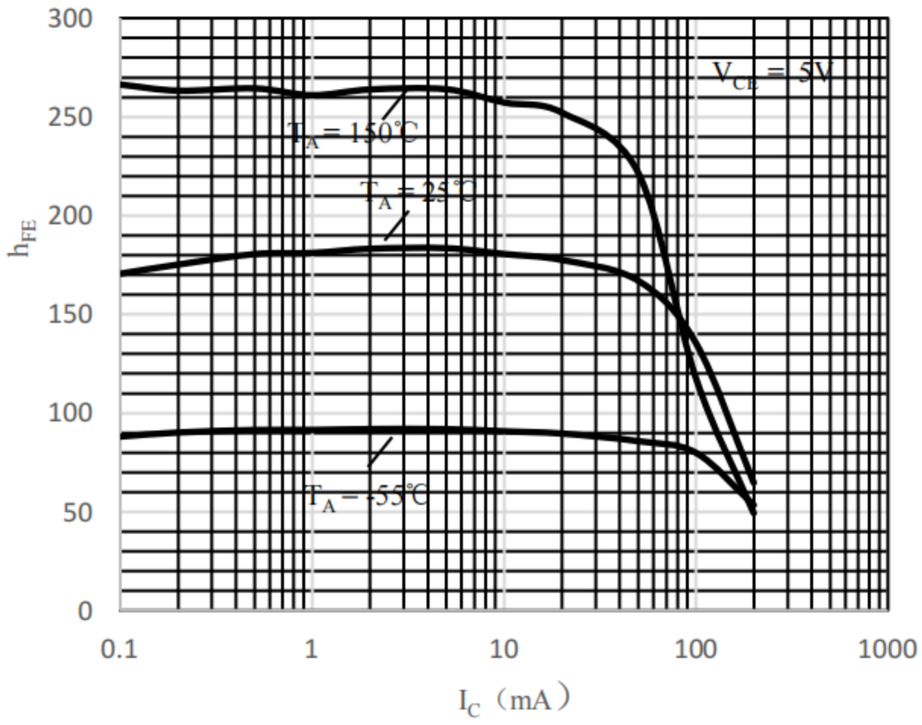


Fig 1 h_{FE} vs. I_C

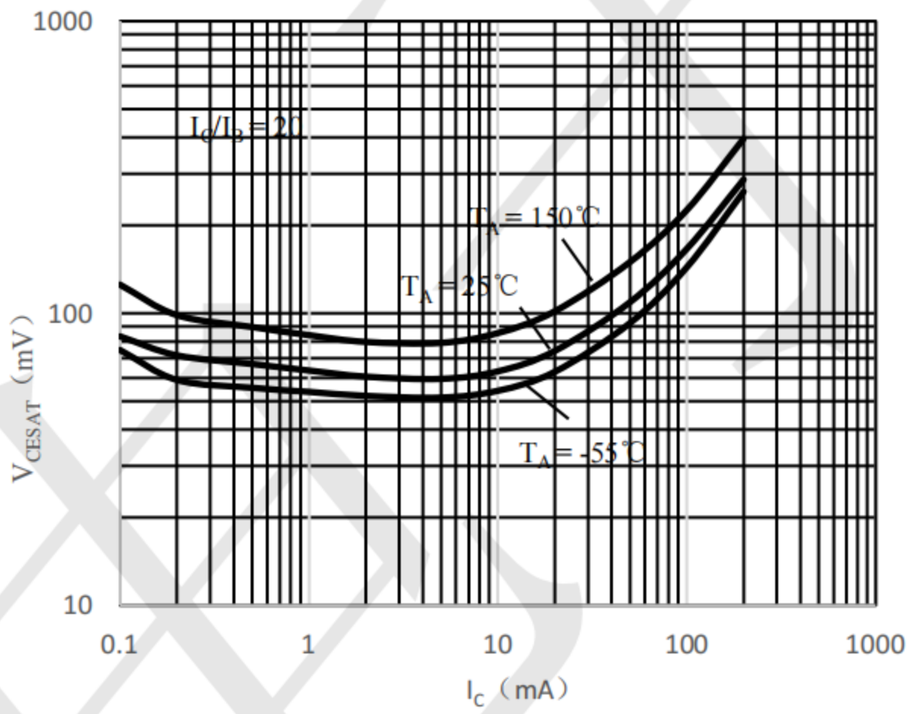


Fig 2 $V_{CE(sat)}$ vs. I_C

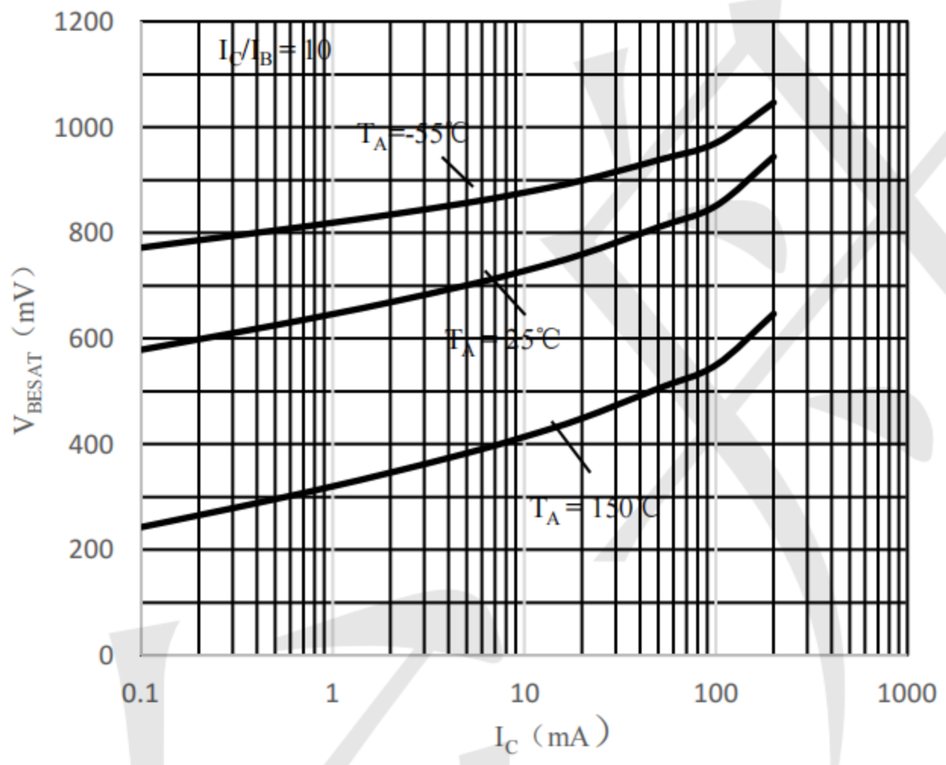


Fig 3 $V_{BE(sat)}$ vs. I_C

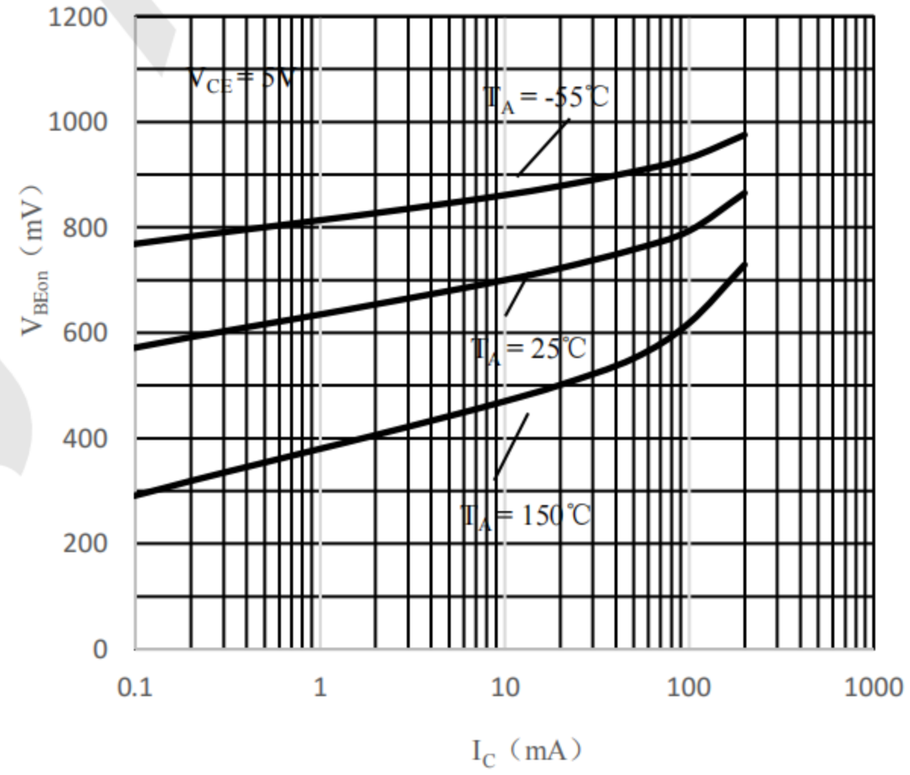


Fig 4 $V_{BE(ON)}$ vs. I_C

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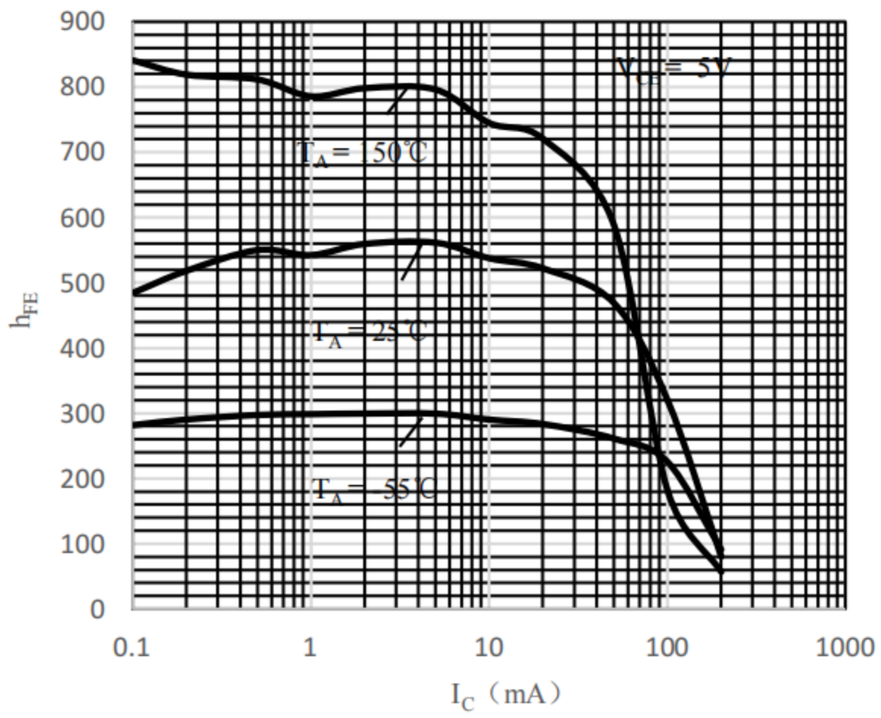

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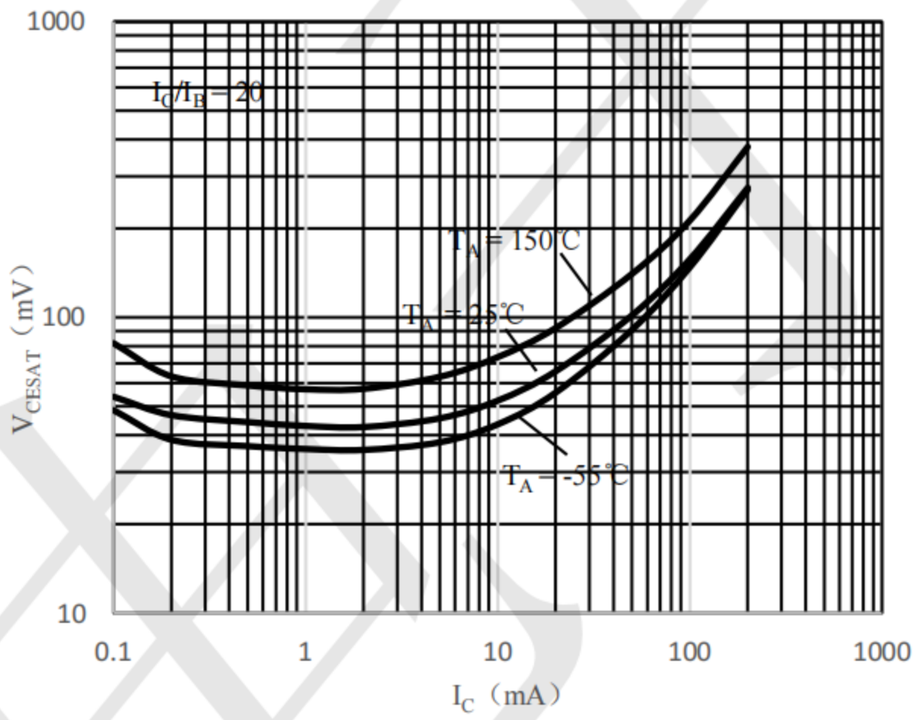

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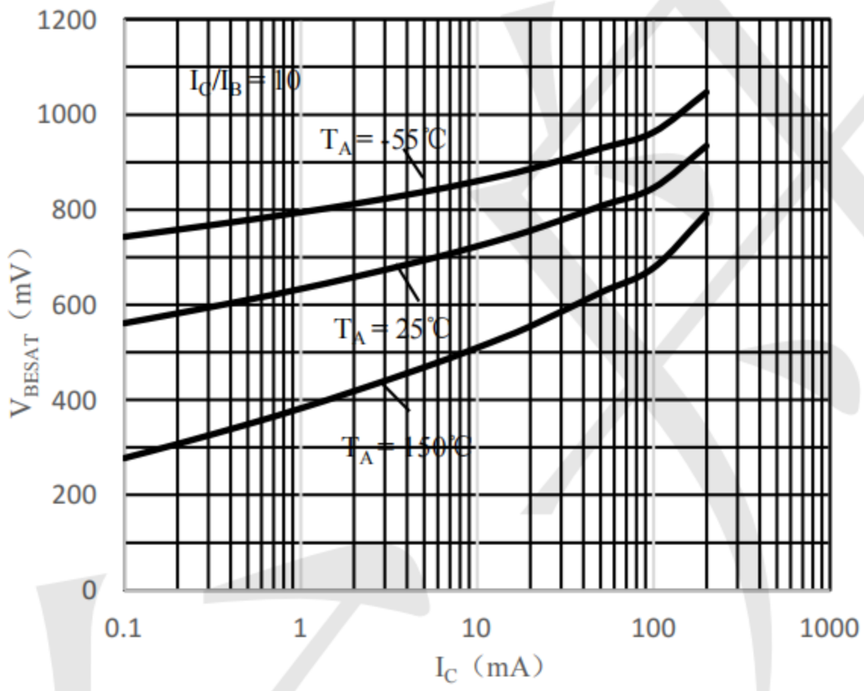

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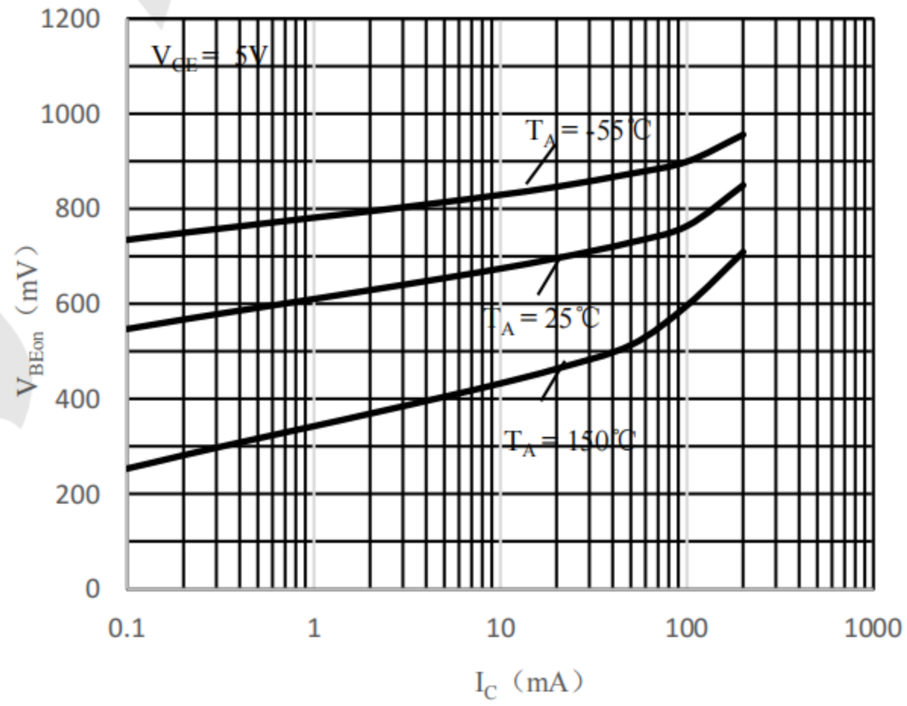

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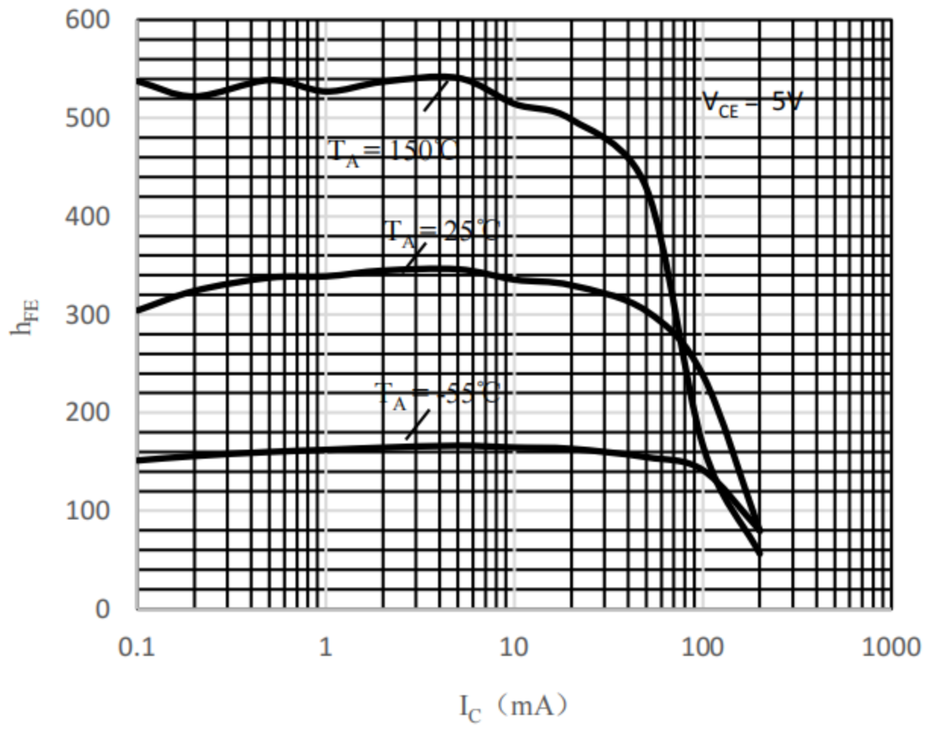

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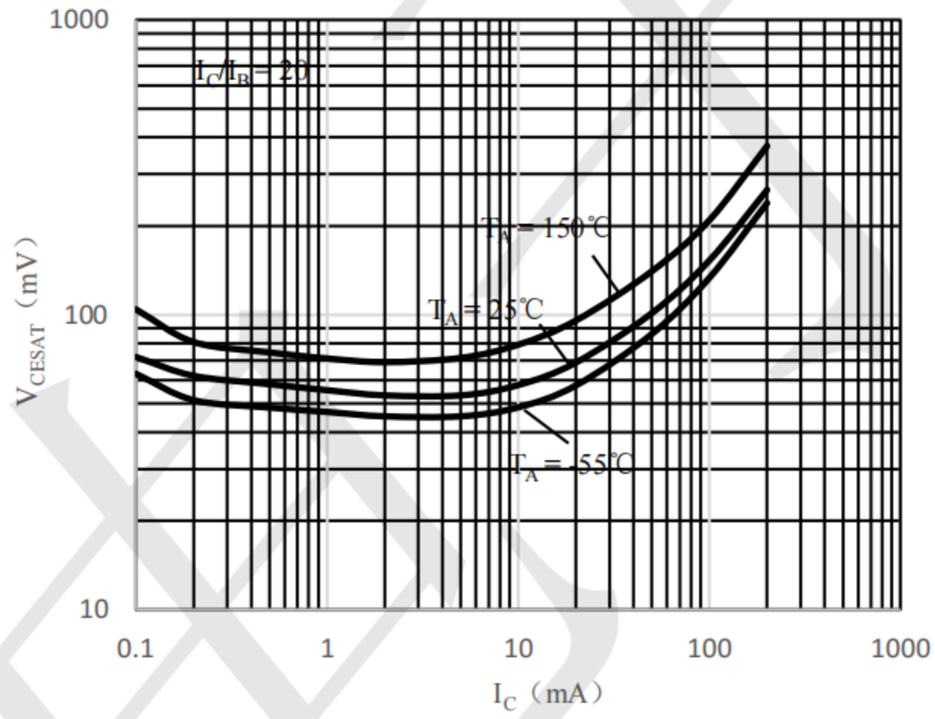

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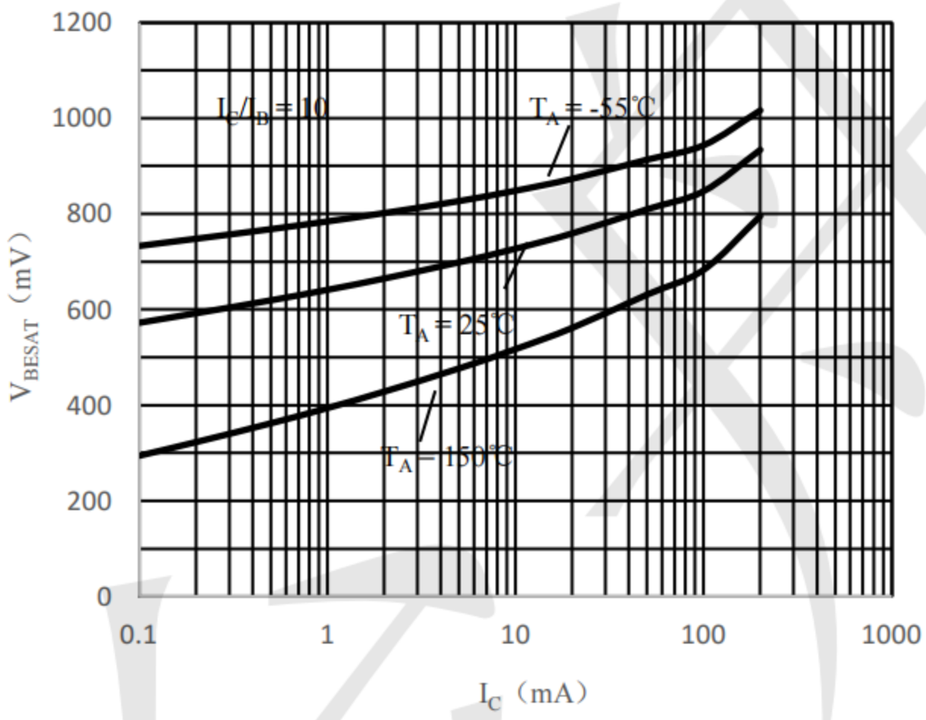

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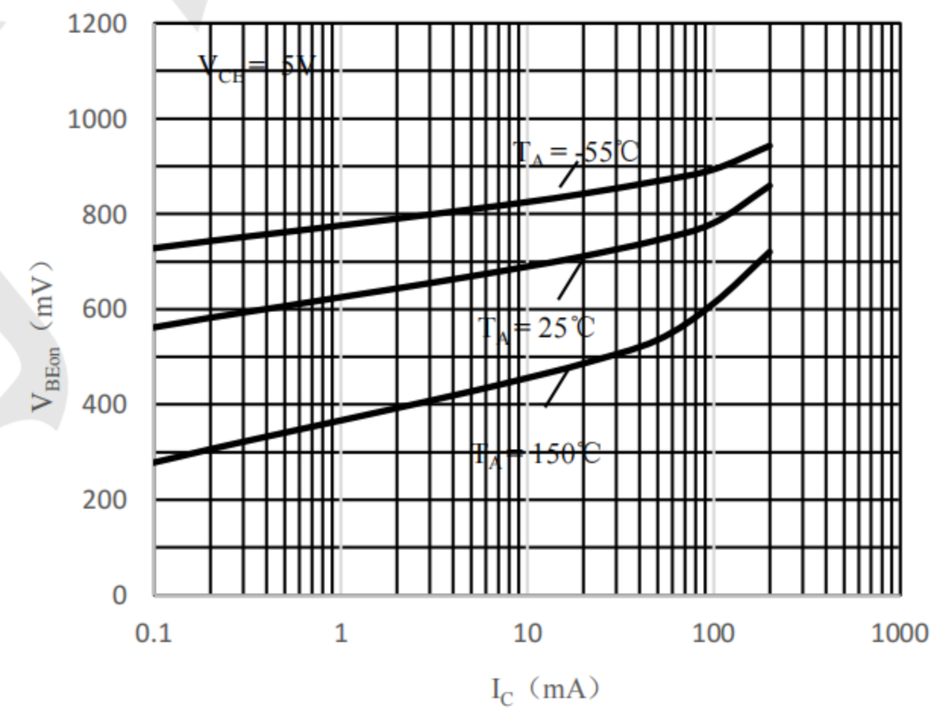

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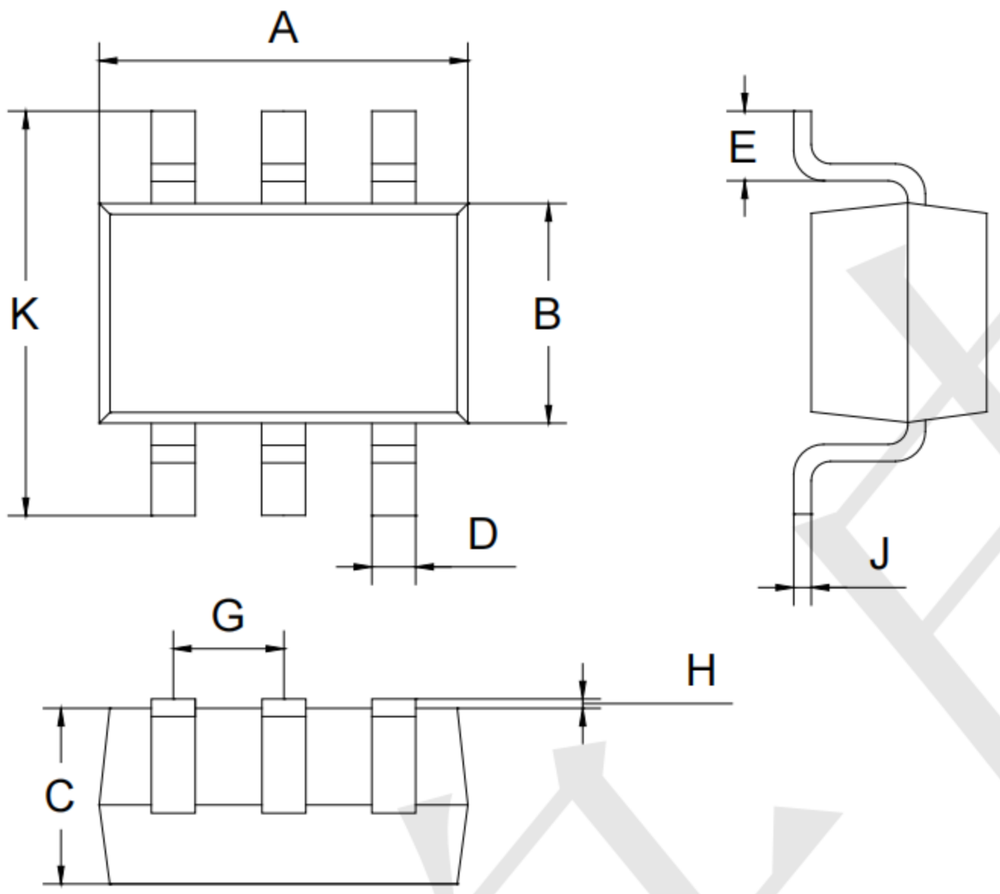
Outline Drawing - SOT363 (unit: mm)



SOT-363		
Dim	Min	Max
A	2.00	2.20
B	1.15	1.35
C	0.85	1.05
D	0.15	0.35
E	0.25	0.40
G	0.60	0.70
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40

Mounting Pad Layout-SOT363 (unit: mm)